Ian W Boyd

List of Publications by Year in descending order

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163 papers	3,849 citations	101543 36 h-index	161849 54 g-index
168 all docs	168 docs citations	168 times ranked	2724 citing authors

#	Article	IF	Citations
1	Characteristics of high quality ZnO thin films deposited by pulsed laser deposition. Applied Physics Letters, 1994, 65, 2963-2965.	3.3	264
2	Nanocrystalline TiO2 films studied by optical, XRD and FTIR spectroscopy. Journal of Non-Crystalline Solids, 2002, 303, 134-138.	3.1	163
3	Laser Processing of Thin Films and Microstructures. Springer Series in Materials Science, 1987, , .	0.6	130
4	Efficient excimer ultraviolet sources from a dielectric barrier discharge in rareâ€gas/halogen mixtures. Journal of Applied Physics, 1996, 80, 633-638.	2.5	105
5	Pulsed-laser deposited ZnO for device applications. Applied Surface Science, 1996, 96-98, 811-818.	6.1	93
6	Siliconâ€silicon dioxide interface: An infrared study. Journal of Applied Physics, 1987, 62, 3195-3200.	2.5	92
7	New large area ultraviolet lamp sources and their applications. Nuclear Instruments & Methods in Physics Research B, 1997, 121, 349-356.	1.4	83
8	Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition. Applied Surface Science, 1995, 86, 99-106.	6.1	74
9	FTIR and XPS investigation of Er-doped SiO2â€“TiO2 films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 209-213.	3.5	70
10	Efficient XeI* excimer ultraviolet sources from a dielectric barrier discharge. Journal of Applied Physics, 1998, 84, 1174-1178.	2.5	69
11	Deconvolution of the infrared absorption peak of the vibrational stretching mode of silicon dioxide: Evidence for structural order?. Applied Physics Letters, 1987, 51, 418-420.	3.3	67
12	Photo-induced growth of dielectrics with excimer lamps. Solid-State Electronics, 2001, 45, 1413-1431.	1.4	66
13	Nonlinear-optical energy regulation by nonlinear refraction and absorption in silicon. Optics Letters, 1984, 9, 291.	3.3	65
14	Decomposition mechanisms of thin palladium acetate film with excimer UV radiation. Applied Surface Science, 1996, 96-98, 399-404.	6.1	59
15	Light emission from germanium nanoparticles formed by ultraviolet assisted oxidation of siliconâ€germanium. Applied Physics Letters, 1996, 69, 1506-1508.	3.3	58
16	Laserâ€enhanced oxidation of Si. Applied Physics Letters, 1983, 42, 728-730.	3.3	57
17	Growth of tantalum pentoxide film by pulsed laser deposition. Applied Surface Science, 1999, 138-139, 320-324.	6.1	57
18	Interface of ultrathin HfO2 films deposited by UV-photo-CVD. Thin Solid Films, 2004, 453-454, 203-207.	1.8	56

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19	Vacuum-Ultra-Violet and Ozone Induced Oxidation of Silicon and Silicon-Germanium. Japanese Journal of Applied Physics, 1993, 32, 6141-6146.	1.5	53
20	UV curing of optical fibre coatings using excimer lamps. Applied Surface Science, 2002, 186, 568-572.	6.1	52
21	Low temperature photo-oxidation of silicon using a xenon excimer lamp. Applied Physics Letters, 1997, 71, 2964-2966.	3.3	50
22	Investigation of TiO2-doped HfO2 thin films deposited by photo-CVD. Thin Solid Films, 2003, 428, 263-268.	1.8	50
23	Thin tantalum pentoxide films deposited by photo-induced CVD. Thin Solid Films, 1998, 336, 340-343.	1.8	49
24	Characteristics of dielectric layers grown on Ge by low temperature vacuum ultraviolet-assisted oxidation. Applied Physics Letters, 1999, 75, 1261-1263.	3.3	48
25	Structure of ultrathin silicon dioxide films. Applied Physics Letters, 1987, 50, 320-322.	3.3	47
26	Characteristics of high quality tantalum oxide films deposited by photoinduced chemical vapor deposition. Applied Physics Letters, 1998, 73, 2299-2301.	3.3	47
27	Ozoneâ€induced rapid low temperature oxidation of silicon. Applied Physics Letters, 1993, 63, 2517-2519.	3.3	45
28	Low pressure photodeposition of silicon nitride films using a xenon excimer lamp. Applied Physics Letters, 1993, 63, 1757-1759.	3.3	43
29	Titanium dioxide films prepared by photo-induced solâ€“gel processing using 172 nm excimer lamps. Surface and Coatings Technology, 2000, 125, 424-427.	4.8	43
30	Various phase transitions and changes in surface morphology of crystalline silicon induced by 4â€“260â€ps pulses of 1â€Î¼m radiation. Applied Physics Letters, 1984, 45, 80-82.	3.3	41
31	Thin film growth by pulsed laser deposition. Ceramics International, 1996, 22, 429-434.	4.8	39
32	Thin tantalum oxide films prepared by 172 nm Excimer lamp irradiation using solâ€“gel method. Thin Solid Films, 1998, 318, 252-256.	1.8	39
33	Lifetime investigation of excimer UV sources. Applied Surface Science, 2000, 168, 296-299.	6.1	39
34	Growth and modeling of cwâ€UV induced oxidation of silicon. Journal of Applied Physics, 1994, 75, 227-231.	2.5	38
35	Growth rate enhancement using ozone during rapid thermal oxidation of silicon. Applied Physics Letters, 1994, 65, 412-414.	3.3	37
36	Pulsed laser deposition of novel materials for thin film solid oxide fuel cell applications: Ce 0.9 Gd 0.1 O 1.95 , La 0.7 Sr 0.3 CoO y and La 0.7 Sr 0.3 Co 0.2 Fe 0.8 O y. Applied Surface Science, 1996, 96-98, 795-801.	6.1	36

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37	Thin tantalum and tantalum oxide films grown by pulsed laser deposition. Applied Surface Science, 2000, 168, 234-238.	6.1	35
38	Characterisation of TiO2 deposited by photo-induced chemical vapour deposition. Applied Surface Science, 2002, 186, 241-245.	6.1	35
39	Characterisation of HfO2 deposited by photo-induced chemical vapour deposition. Thin Solid Films, 2003, 427, 391-396.	1.8	35
40	Low temperature synthesis of Ge nanocrystals in SiO2. Applied Physics Letters, 1994, 65, 3233-3235.	3.3	33
41	Rapid photochemical deposition of silicon dioxide films using an excimer lamp. Journal of Applied Physics, 1994, 76, 4372-4376.	2.5	33
42	Rapid photo-oxidation of silicon at room temperature using 126 nm vacuum ultraviolet radiation. Applied Surface Science, 2002, 186, 64-68.	6.1	33
43	Formation of High Quality Tantalum Oxide Thin Films at 400Â°C by 172 nm Radiation. Japanese Journal of Applied Physics, 1998, 37, L27-L29.	1.5	32
44	Characteristic photoluminescence properties of Si nanocrystals in SiO2 fabricated by ion implantation and annealing. Solid-State Electronics, 2001, 45, 1487-1494.	1.4	29
45	Vacuum ultraviolet annealing of hydroxyapatite films grown by pulsed laser deposition. Journal of Applied Physics, 1999, 85, 8410-8414.	2.5	28
46	Low dielectric constant porous silica films formed by photo-induced solâ€“gel processing. Materials Science in Semiconductor Processing, 2000, 3, 345-349.	4.0	28
47	VUV light-induced decomposition of palladium acetate films for electroless copper plating. Applied Surface Science, 1997, 109-110, 487-492.	6.1	26
48	Investigations of photo-induced decomposition of palladium acetate for electroless copper plating. Thin Solid Films, 1998, 318, 234-238.	1.8	26
49	Ultrathin high-quality tantalum pentoxide films grown by photoinduced chemical vapor deposition. Applied Physics Letters, 2000, 77, 3574-3576.	3.3	26
50	Giant magnetoresistance behaviour in in-situ La0.60Sr0.40MnO3 films grown on Si substrates by pulsed laser deposition. Applied Surface Science, 1997, 109-110, 350-353.	6.1	25
51	Ultrathin silicon dioxide films grown by photo-oxidation of silicon using 172 nm excimer lamps. Applied Surface Science, 2000, 168, 288-291.	6.1	25
52	Laser processing of silicon. Nature, 1983, 303, 481-486.	27.8	24
53	UV intensity measurement of 308 nm excimer lamp using chemical actinometer. Applied Surface Science, 1999, 138-139, 315-319.	6.1	24
54	Structural changes produced in silicon by intense 1â€¼mâ€‰ps pulses. Journal of Applied Physics, 1986, 60, 1169-1182.	2.5	23

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55	Composition dependence of electronic structure and optical properties of Hf1â^'xSixOy gate dielectrics. Journal of Applied Physics, 2008, 104, 104116.	2.5	23
56	Laser-ablation deposition of uniform thin films of Bi2Sr2CaCu2Ox. Applied Surface Science, 1990, 46, 84-88.	6.1	22
57	Structural and electrical properties of tantalum oxide films grown by photo-assisted pulsed laser deposition. Applied Surface Science, 2002, 186, 40-44.	6.1	22
58	Stiffness memory nanohybrid scaffolds generated by indirect 3D printing for biologically responsive soft implants. Acta Biomaterialia, 2018, 80, 188-202.	8.3	22
59	Energy-dispersive mass spectrometry of high energy ions generated during KrF excimer and frequency-doubled Nd:YAG laser ablation of metals. Applied Surface Science, 1996, 96-98, 227-232.	6.1	21
60	UV light-induced deposition of low dielectric constant organic polymer for interlayer dielectrics. Optical Materials, 1998, 9, 251-254.	3.6	21
61	Palladium nanoparticles on silicon by photo-reduction using 172 nm excimer UV lamps. Applied Surface Science, 2004, 226, 7-11.	6.1	21
62	Photonâ€controlled oxidation of silicon. Applied Physics Letters, 1987, 51, 1149-1151.	3.3	20
63	Fluorine enhanced oxidation of silicon at low temperatures. Applied Physics Letters, 1994, 65, 1572-1574.	3.3	20
64	Vacuum ultraviolet annealing of thin films grown by pulsed laser deposition. Applied Surface Science, 1999, 138-139, 587-592.	6.1	20
65	High-k dielectrics by UV photo-assisted chemical vapour deposition. Microelectronic Engineering, 2003, 66, 621-630.	2.4	20
66	Growth of titanium silicate thin films by photo-induced chemical vapor deposition. Thin Solid Films, 2004, 453-454, 167-171.	1.8	20
67	Surface modification of polyimide with excimer UV radiation at wavelength of 126 nm. Thin Solid Films, 2004, 453-454, 3-6.	1.8	20
68	Low temperature VUV enhanced growth of thin silicon dioxide films. Applied Surface Science, 1990, 46, 352-356.	6.1	19
69	Stress effect and enhanced magnetoresistance inLa0.67Ca0.33MnO3â^'Î´films. Physical Review B, 1998, 58, 14143-14146.	3.2	19
70	Low temperature photoformation of tantalum oxide. Microelectronics Reliability, 2000, 40, 649-655.	1.7	19
71	Hf1â^'xSixOy dielectric films deposited by UV-photo-induced chemical vapour deposition (UV-CVD). Applied Surface Science, 2007, 253, 7869-7873.	6.1	19
72	Pulsewidth-dependence of nonlinear energy deposition and redistribution in Si, GaAs and Ge during 1 Î¼m picosecond irradiation. Journal of Luminescence, 1985, 30, 272-289.	3.1	18

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73	Rapid oxidation of silicon using 126 nm excimer radiation at low pressure. Applied Surface Science, 2003, 208-209, 369-373.	6.1	18
74	Incorporation of carbon dioxide laserâ€grown oxide layers into conventional metalâ€oxideâ€silicon devices. Journal of Applied Physics, 1983, 54, 3561-3565.	2.5	16
75	Temporally resolved imaging of silicon surfaces melted with intense picosecond 1â€Î¼m laser pulses. Applied Physics Letters, 1985, 46, 366-368.	3.3	16
76	Low temperature oxidation of crystalline silicon using excimer laser irradiation. Applied Surface Science, 1989, 36, 134-140.	6.1	16
77	Transport properties and giant magnetoresistance behavior in Laâ€Ndâ€Srâ€Mnâ€O films. Applied Physics Letters, 1996, 69, 1154-1156.	3.3	16
78	Incongruent transfer related to surface segregation in pulsed-laser-deposited Laâ€“Caâ€“Mnâ€“O films. Applied Physics Letters, 1998, 73, 2745-2747.	3.3	16
79	Synthesis of (BiPb)2Sr2Ca2Cu3O10superconducting thin films on MgO using a multilayered pulsed laser deposition method. Applied Physics Letters, 1993, 63, 3373-3375.	3.3	15
80	Characterization of Lead-Zirconate-Titanate (PZT) Films Formed by Photo-Decomposition of Metal Organic Polymer. Japanese Journal of Applied Physics, 1999, 38, L393-L394.	1.5	15
81	SEM observations of YBCO on as-received and heat-treated MgO substrates. Applied Surface Science, 1995, 86, 134-139.	6.1	14
82	Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films. Applied Surface Science, 1996, 96-98, 769-774.	6.1	14
83	Ultraviolet annealing of tantalum oxide films grown by photo-induced chemical vapour deposition. Journal Physics D: Applied Physics, 1999, 32, L91-L95.	2.8	14
84	Kinetic study of 222 nm excimer lamp induced decomposition of palladium-acetate films. Applied Surface Science, 1999, 138-139, 401-407.	6.1	14
85	Photo-induced preparation of (Ta2O5)1â^'x(TiO2)x dielectric thin films using solâ€“gel processing with xenon excimer lamps. Applied Surface Science, 2000, 168, 13-16.	6.1	14
86	A review of laser beam applications for processing silicon. Contemporary Physics, 1983, 24, 461-490.	1.8	13
87	Low temperature UV oxidation of SiGe for preparation of Ge nanocrystals in SiO2. Thin Solid Films, 1995, 255, 290-294.	1.8	13
88	Characterisation of ultraviolet annealed tantalum oxide films deposited by photo-CVD using 172 nm excimer lamp. Materials Science in Semiconductor Processing, 2001, 4, 313-317.	4.0	13
89	Characterisation of ionic species generated during ablation of Bi2Sr2Ca2Cu3O10 by frequency-doubled Nd:YAG laser irradiation. Applied Surface Science, 1995, 86, 50-58.	6.1	12
90	Growth of giant magnetoresistance metallic granular CoAg films by pulsed laser deposition. Journal of Magnetism and Magnetic Materials, 1997, 165, 330-333.	2.3	12

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91	Thermoresponsive Stiffness Softening of Hierarchically Porous Nanohybrid Membranes Promotes Niches for Mesenchymal Stem Cell Differentiation. Advanced Healthcare Materials, 2019, 8, e1801556.	7.6	12
92	Growth of pure and doped cerium oxide thin film bilayers by pulsed laser deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 34, 192-198.	3.5	11
93	Growth of perovskite manganite oxide thin films by PLD. Applied Surface Science, 1998, 127-129, 410-417.	6.1	11
94	Deposition and annealing of tantalum pentoxide films using 172 nm excimer lamp. Applied Surface Science, 2000, 154-155, 382-386.	6.1	11
95	Ultraviolet annealing of thin films grown by pulsed laser deposition. Applied Surface Science, 2000, 154-155, 17-21.	6.1	10
96	Interface of tantalum oxide films on silicon by UV annealing at low temperature. Thin Solid Films, 2003, 428, 248-252.	1.8	10
97	Incorporation of oxygen atoms into As+ implanted silicon during cw CO2 laser annealing in O2. Applied Physics A: Solids and Surfaces, 1983, 31, 71-74.	1.4	9
98	Photo-chemical production of gold nanoparticles in monolithic porous silica by using a novel excimer ultraviolet source. Inorganic Chemistry Communication, 2003, 6, 950-952.	3.9	9
99	Enhancement of luminescence from encapsulated Si nanocrystals in SiO2 with rapid thermal anneals. Nuclear Instruments & Methods in Physics Research B, 2005, 230, 203-209.	1.4	9
100	Photo-induced Large Area Growth Of Dielectrics With Excimer Lamps. Materials Research Society Symposia Proceedings, 2000, 617, 441.	0.1	8
101	Advanced low-energy durable coatings. International Journal of Energy Research, 2015, 39, 165-171.	4.5	8
102	Low Temperature Si Oxidation with Excimer Lamp Sources. Materials Research Society Symposia Proceedings, 1997, 470, 343.	0.1	7
103	Ultraviolet induced mechanisms in oxide film formation. Applied Surface Science, 1997, 109-110, 538-543.	6.1	7
104	Excimer lamp-induced decomposition of platinum acetylacetonate films for electroless copper plating. Solid-State Electronics, 1999, 43, 1107-1111.	1.4	7
105	Photo-deposition of tantalum pentoxide film using 222 nm excimer lamps. Applied Surface Science, 2000, 168, 307-311.	6.1	7
106	(Ta2O5)1âˆ'x(TiO2)x deposited by photo-induced CVD using 222 nm excimer lamps. Applied Surface Science, 2002, 186, 246-250.	6.1	7
107	Visible photoluminescence from nanocrystalline Ge grown at room temperature by photo-oxidation of SiGe using a 126 nm lamp. Applied Surface Science, 2003, 208-209, 364-368.	6.1	7
108	Geometric optimisation for the deposition of high temperature superconductors. Applied Surface Science, 1989, 43, 382-386.	6.1	6

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109	Evolution of the morphology of annealed, bulk mgo (100) substrate surfaces. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 37, 162-167.	3.5	6
110	Effect of trivalent ion composition on the magnetoresistance behavior of LaxNd0.6â^'xSr0.40MnO3â^'Î´films. Applied Physics Letters, 1996, 69, 3599-3601.	3.3	6
111	Development of Large area Excimer VUV and UV Sources from a Dielectric Barrier Discharge. Materials Research Society Symposia Proceedings, 1997, 471, 53.	0.1	6
112	Characteristics of dielectric layers formed by low-temperature vacuum ultraviolet-assisted oxidation of SiGe layers. Journal of Materials Research, 1999, 14, 3525-3529.	2.6	6
113	New assessment criteria for durability evaluation of highly repellent surfaces. Wear, 2017, 390-391, 49-60.	3.1	6
114	Laser Assisted Pyrolytic Growth and Photochemical Deposition of Thin Oxide Films. Springer Series in Chemical Physics, 1984, , 274-287.	0.2	6
115	ULSI dielectrics: low-temperature silicon dioxides. Materials Chemistry and Physics, 1995, 41, 266-274.	4.0	5
116	Stress effects induced in SiGe strained layers by low-temperature ultraviolet-assisted oxidation. Journal of Applied Physics, 1998, 83, 1770-1772.	2.5	5
117	Formation of silicon dioxide layers during UV annealing of tantalum pentoxide film. Applied Surface Science, 2000, 168, 312-315.	6.1	5
118	Challenges in the Oxidation of Strained SiGe Layers. , 1998, , 461-475.		5
119	Initial Obsevation of the Crystal-Amorphous Transition and the Formation of Ripple Patterns on Silicon Induced by 7 ps Pulses at 1.05 Âµm. Materials Research Society Symposia Proceedings, 1983, 23, 203.	0.1	4
120	Spatial And Temporal Resolution Of The Nonlinear Optical Properties And Melt Dynamics Of Si At 1 Î¼m. , 1985, , .		4
121	Enhanced magnetoresistance behaviour in CeO2 buffered LaCaMnO films on Si. Applied Surface Science, 1999, 138-139, 563-568.	6.1	4
122	Development and Applications of UV Excimer Lamps. , 2003, , 161-199.		4
123	Photo-Oxidation of Silicon: Reaction Mechanisms and Film Structure. Materials Research Society Symposia Proceedings, 1987, 105, 23.	0.1	3
124	Laser ablation deposition of PbO/BiPbSrCaCuO. Applied Surface Science, 1992, 54, 154-159.	6.1	3
125	<title>Photo-CVD of dielectric materials by pseudo-continuous excimer sources</title>. , 1994, , .		3
126	<title>Photoinduced growth of dielectrics with excimer lamps</title>. , 2000, , .		3

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127	Development and application of UV excimer lamps from 354nm -126nm. , 2006, , .		3
128	Doping and Oxidation. , 1989, , 539-580.		3
129	Optically Enhanced Oxidation. , 1987, , 409-426.		3
130	Thin Film Growth by Pulsed Laser Deposition. , 1994, , 349-359.		2
131	Phase segregation and giant magnetoresistance behavior in as-deposited Co-Ag film grown by pulsed laser deposition. Journal of Applied Physics, 1997, 81, 5211-5213.	2.5	2
132	Photonic effects during low-temperature ultraviolet-assisted oxidation of SiGe. Journal of Electronic Materials, 2002, 31, 1325-1329.	2.2	2
133	The next twenty years. Nature Materials, 2003, 2, 563-565.	27.5	2
134	Electrical characterization of photo-oxidized Si1â^'xâ^'yGexCy films. Microelectronic Engineering, 2004, 72, 218-222.	2.4	2
135	Deposition and growth kinetics studies of thin zirconium dioxide films by UVILS-CVD. Applied Surface Science, 2007, 253, 7942-7946.	6.1	2
136	Optical Regulation Using Crystalline Silicon. Springer Series in Chemical Physics, 1984, , 50-53.	0.2	2
137	Confirmation of the Wavelength Dependence of Silicon Oxidation Induced by Visible Radiation. , 1988, , 171-178.		2
138	Semiconductor technology: Kinetics of pulsed laser annealing. Nature, 1985, 313, 100-100.	27.8	1
139	Ultrathin Silicon Dioxide Films: Photo-Induced Growth. Materials Research Society Symposia Proceedings, 1988, 129, 421.	0.1	1
140	Mechanisms of droplet formation in pulsed laser growth of thin oxide films. , 1998, , .		1
141	Photo-Induced Growth of Low Dielectric Constant Porous Silica Film at Room Temperature. Materials Research Society Symposia Proceedings, 2000, 612, 5171.	0.1	1
142	Excimer ultraviolet sources for thin film deposition: a 15 year perspective. , 2010, , .		1
143	Laser-Assisted Oxidation and Nitridation. Springer Series in Materials Science, 1987, , 134-189.	0.6	1
144	Material Removal. Springer Series in Materials Science, 1987, , 236-271.	0.6	1

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145	Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films. , 1996, , 769-774.		1
146	Spatially and Temporally Resolved Reflectivity Profiles of Crystalline Silicon Irradiated by 48 Ps Pulses of One-Micron Laser Radiation. Materials Research Society Symposia Proceedings, 1984, 35, 107.	0.1	0
147	Cross-Sectional Tem Characterization of Structural Changes Produced In Silicon By One Micron Picosecond Pulses. Materials Research Society Symposia Proceedings, 1985, 51, 213.	0.1	0
148	Experimental Considerations. Springer Series in Materials Science, 1987, , 100-133.	0.6	0
149	Photoformation of dielectrics. Applied Physics A: Materials Science and Processing, 1988, 46, 241-241.	2.3	0
150	Low Temperature UV Growth of SiO2 in O2 and N2O. Materials Research Society Symposia Proceedings, 1991, 236, 371.	0.1	0
151	Microstructure of Pulsed-Laser Deposited Pzt on Polished and Annealed Mgo Substrates. Materials Research Society Symposia Proceedings, 1996, 433, 157.	0.1	0
152	Enhanced magnetoresistance in Laî—¸Caî—¸Mnî—¸O films on Si substrates using YBaCuO/CeO2 heterostructures. Physica C: Superconductivity and Its Applications, 1997, 282-287, 1231-1232.	1.2	0
153	Photo-Induced Large Area Growth of Dielectrics With Excimer Lamps. Materials Research Society Symposia Proceedings, 2000, 624, 115.	0.1	0
154	Characterisation of TiO2 films grown at low temperatures for alternative gate dielectric application. Materials Research Society Symposia Proceedings, 2001, 670, 1.	0.1	0
155	PULSEWIDTH-DEPENDENCE OF NONLINEAR ENERGY DEPOSITION AND REDISTRIBUTION IN Si, GaAs AND Ge DURING 1 Î¼m PICOSECOND IRRADIATION. , 1985, , 272-289.		0
156	Interactions and Kinetics. Springer Series in Materials Science, 1987, , 15-99.	0.6	0
157	Passivation by Laser Annealing and Melting. Springer Series in Materials Science, 1987, , 190-208.	0.6	0
158	Growth and Structure of Argon Laser Grown SiO2. , 1988, , 331-336.		0
159	Thin film growth by pulsed laser deposition. , 1994, , 319-326.		0
160	Evolution of the morphology of annealed, bulk MgO (100) substrate surfaces. , 1996, , 162-167.		0
161	Pulsed-laser deposited ZnO for device applications. , 1996, , 811-818.		0
162	Energy-dispersive mass spectrometry of high energy ions generated during KrF excimer and frequency-doubled Nd:YAG laser ablation of metals. , 1996, , 227-232.		0

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163	Pulsed laser deposition of novel materials for thin film solid oxide fuel cell applications: Ce0.9Gd0.1O1.95, La0.7Sr0.3CoOy and La0.7Sr0.3Co0.2Fe0.8Oy. , 1996, , 795-801.		0